



STD7NS20 STD7NS20-1

N-CHANNEL 200V - 0.35Ω - 7A DPAK / IPAK MESH OVERLAY™ MOSFET

PRELIMINARY DATA

TYPE	V _{DSS}	R _{DS(on)}	I _D
STD7NS20	200 V	< 0.40 Ω	7 A
STD7NS20-1	200 V	< 0.40 Ω	7 A

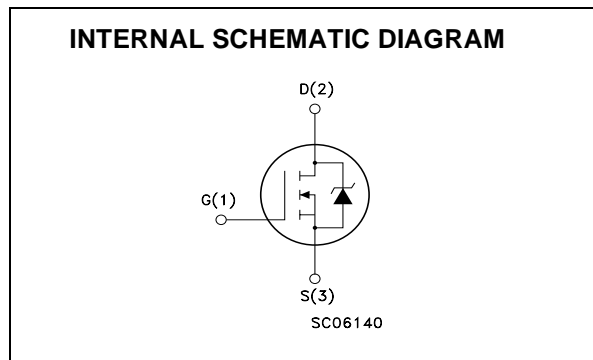
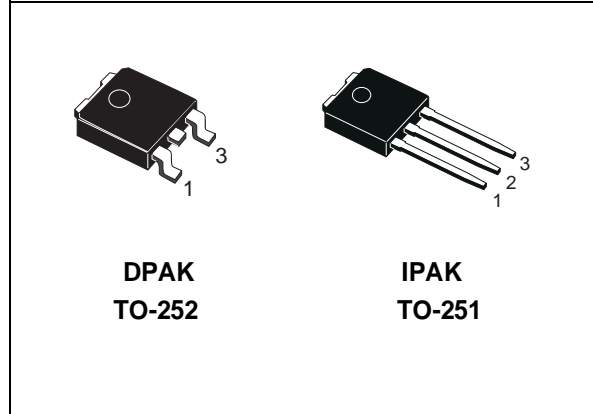
- TYPICAL R_{DS(on)} = 0.35 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- VERY LOW INTRINSIC CAPACITANCES
- ADD SUFFIX "T4" FOR ORDERING IN TAPE & REEL

DESCRIPTION

Using the latest high voltage MESH OVERLAY™ process, STMicroelectronics has designed an advanced family of power MOSFETs with outstanding performance. The new patented STRIP layout coupled with the Company's proprietary edge termination structure, makes it suitable in converters for lighting applications.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SWITCH MODE POWER SUPPLIES (SMPS)
- DC-DC CONVERTERS FOR TELECOM, INDUSTRIAL, AND LIGHTING EQUIPMENT



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	200	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	200	V
V _{GS}	Gate- source Voltage	± 20	V
I _D	Drain Current (continuous) at T _C = 25°C	7	A
I _D	Drain Current (continuous) at T _C = 100°C	4.4	A
I _{DM} (*)	Drain Current (pulsed)	28	A
P _{TOT}	Total Dissipation at T _C = 25°C	45	W
	Derating Factor	0.37	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	5	V/ns
T _{stg}	Storage Temperature	-65 to 150	°C
T _j	Max. Operating Junction Temperature	150	°C

(*) Pulse width limited by safe operating area

(1) I_{SD} ≤ 7A, di/dt ≤ 300 A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ T_{JMAX}

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THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	2.7	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	100	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose	275	°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max)	7	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 50 V)	60	mJ

ELECTRICAL CHARACTERISTICS (TCASE = 25 °C UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	200			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating, T _C = 125 °C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ±20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10V, I _D = 3.5 A		0.35	0.40	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (1)	Forward Transconductance	V _{DS} > I _{D(on)} × R _{DS(on)} max, I _D = 3.5 A		4		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		540		pF
C _{oss}	Output Capacitance			90		pF
C _{rss}	Reverse Transfer Capacitance			35		pF

ELECTRICAL CHARACTERISTICS (CONTINUED)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 100\text{ V}$, $I_D = 3.5\text{ A}$ $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 3)		10		ns
t_r	Rise Time			15		ns
Q_g	Total Gate Charge	$V_{DD} = 160\text{ V}$, $I_D = 18\text{ A}$, $V_{GS} = 10\text{ V}$		31	45	nC
Q_{gs}	Gate-Source Charge			7.5		nC
Q_{gd}	Gate-Drain Charge			9		nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$	Off-voltage Rise Time	$V_{clamp} = 160\text{ V}$, $I_D = 7\text{ A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{ V}$ (see test circuit, Figure 5)		12		ns
t_f	Fall Time			12		ns
t_c	Cross-over Time			25		ns

SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				7	A
$I_{SDM(2)}$	Source-drain Current (pulsed)				28	A
$V_{SD(1)}$	Forward On Voltage	$I_{SD} = 7\text{ A}$, $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 50\text{ V}$, $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		170		ns
Q_{rr}	Reverse Recovery Charge			0.95		μC
I_{RRM}	Reverse Recovery Current			11		A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by safe operating area.

Fig. 1: Unclamped Inductive Load Test Circuit

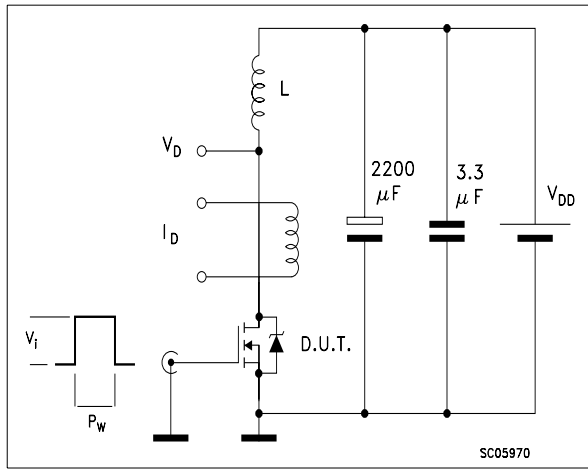


Fig. 2: Unclamped Inductive Waveform

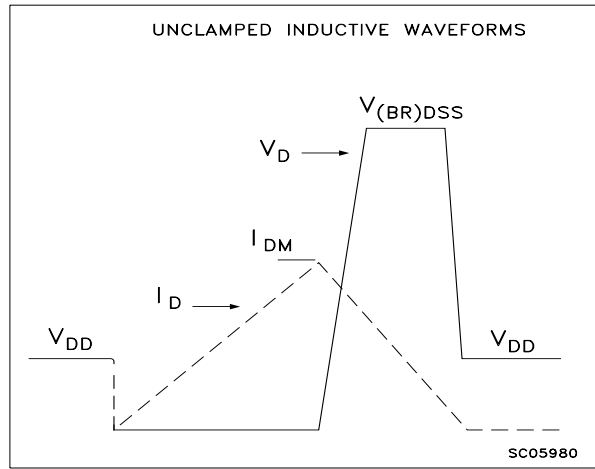


Fig. 3: Switching Times Test Circuit For Resistive Load

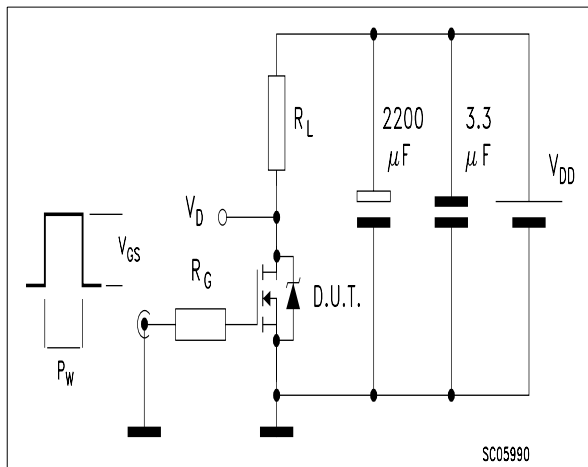


Fig. 4: Gate Charge test Circuit

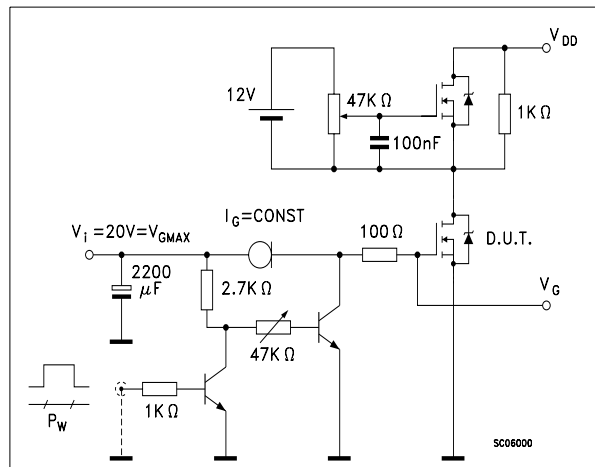
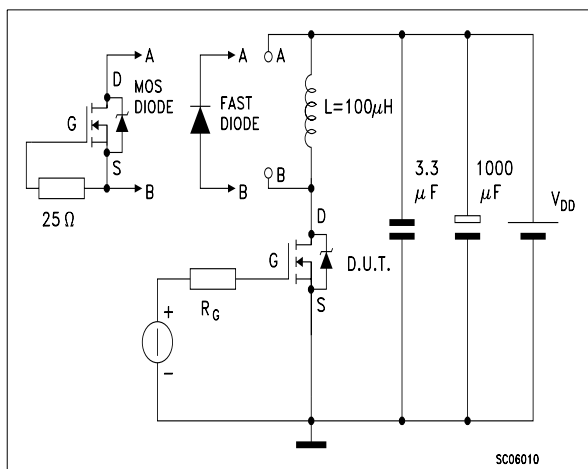
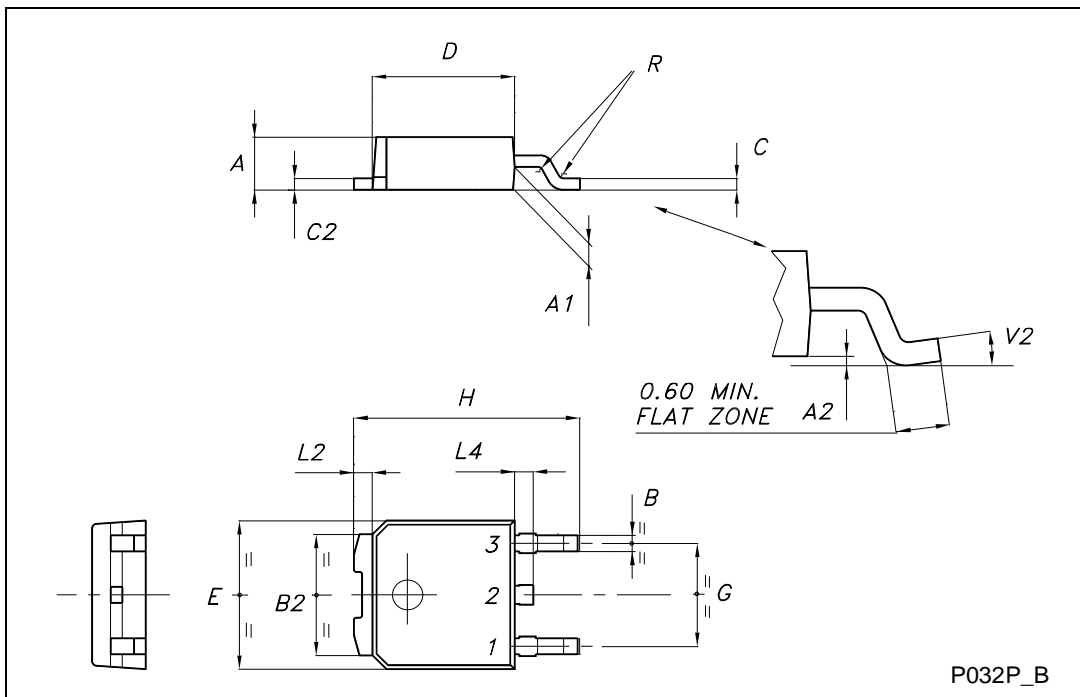


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-252 (DPAK) MECHANICAL DATA

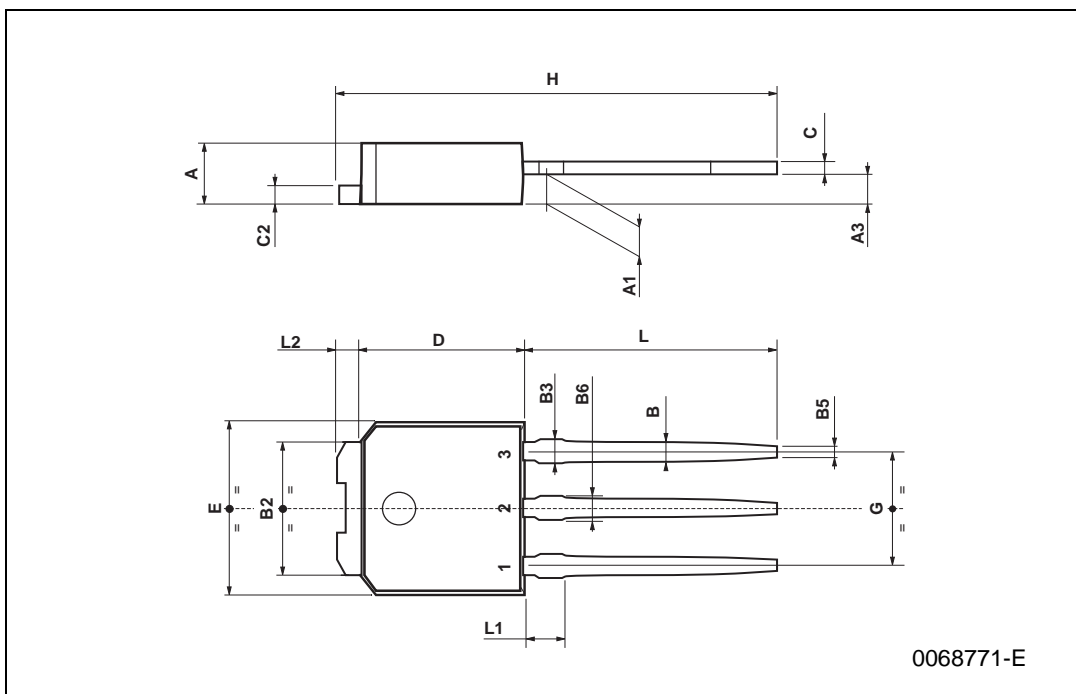
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



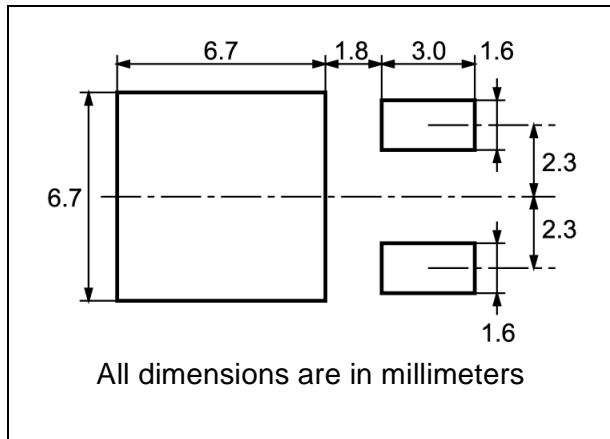
P032P_B

TO-251 (IPAK) MECHANICAL DATA

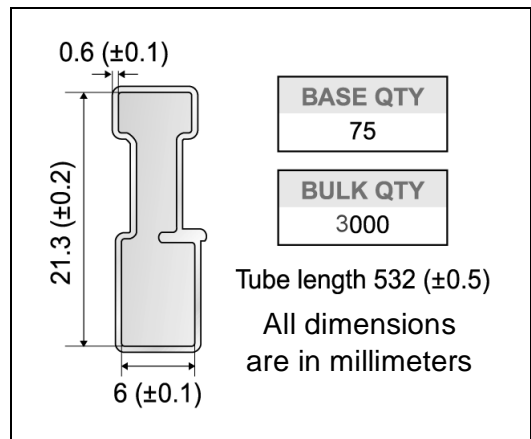
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



DPAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*

REEL MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY	BULK QTY
2500	2500

TAPE MECHANICAL DATA

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

* on sales type



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